

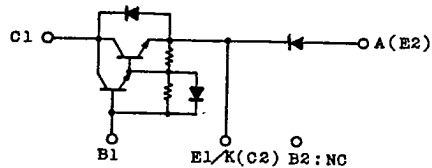
9097250 TOSHIBA (DISCRETE/OPTO)

90D 16260 DT-33-35

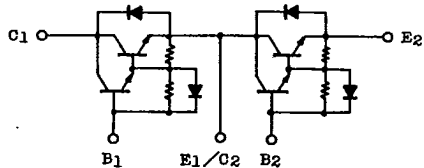


SEMICONDUCTOR
TECHNICAL DATA

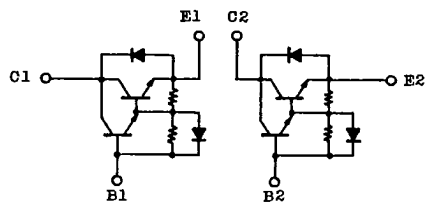
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MG100G2CL1
MG100G2DL1



MG100G1JL1

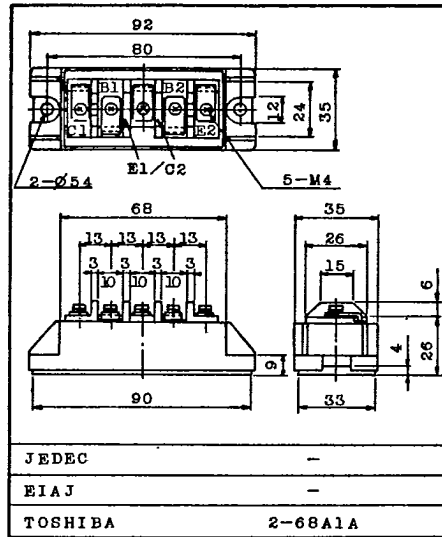


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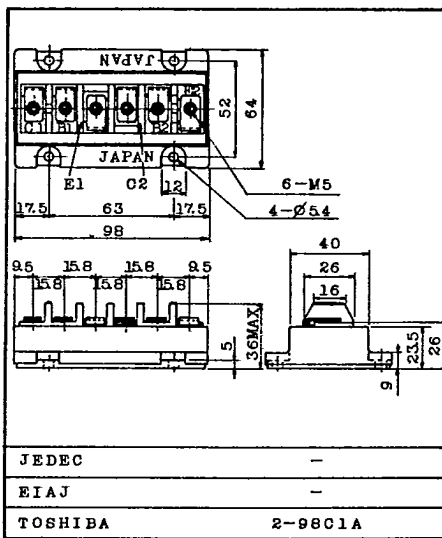


MG100G2DL1

Unit in mm



Unit in mm



TOSHIBA CORPORATION

GT1A2A

9097250 TOSHIBA (DISCRETE/OPTO)

90D 16261

DT-33-35



SEMICONDUCTOR

TECHNICAL DATA

M G 1 0 0 G 1 J L 1
M G 1 0 0 G 2 C L 1
M G 1 0 0 G 2 D L 1

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	600	V
Collector-Emitter Voltage	V _{CE0}	600	V
Collector-Emitter Sustaining Voltage	V _{CE0(SUS)}	450	V
Emitter-Base Voltage	V _{EB0}	6	V
Collector Current	DC	I _C	100
	1ms	I _C	200
	DC	-I _C	100
Base Current	I _B	5	A
Collector Power Dissipation (Tc=25°C)	P _C	400	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-40 ~ 125	°C
Isolation Voltage	V _{isol}	2500(AC 1 Minute)	V
Screw Torque (Terminal/Mounting)	-	20/30	kg.cm

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current	I _{CB0}	V _{CB} =600V, I _E =0	-	-	2.0	mA	
Emitter Cut-off Current	I _{EB0}	V _{EB} =6V, I _C =0	-	-	200	mA	
Collector-Emitter Sustaining Voltage	V _{CE0(SUS)}	I _C =0.5A L=40mH	450	-	-	V	
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =100A	100	-	-	-	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =100A, I _B =2A	-	-	2.0	V	
Base-Emitter Saturation Voltage	V _{BE(sat)}		-	-	2.7	V	
Emitter-Collector Voltage	V _{ECO}	I _E =100A, I _B =0	-	-	1.6	V	
Reverse Recovery Time	t _{rr}	-I _C =100A, V _{EB} =3V V _{CC} =300V, di/dt=100A/μs	-	-	2.0	μs	
Collector Output Capacitance	C _{ob}	V _{CB} =50V, I _E =0 f=1MHz	-	1000	-	pF	
Switching Time	Turn-on Time		-	-	2.0	μs	
	Storage Time		t _{stg}	-	-		12
	Fall Time		t _f	-	-		2.0
Thermal Resistance (Junction to Case)	R _{th(j-c)}	Transistor	-	-	0.31	°C/W	
		Diode	-	-	1.3		

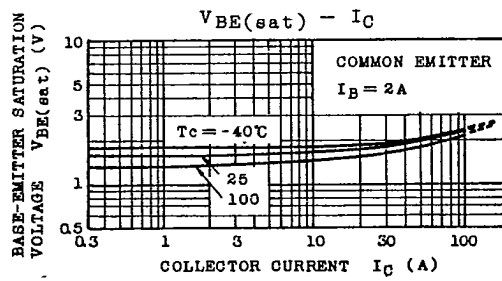
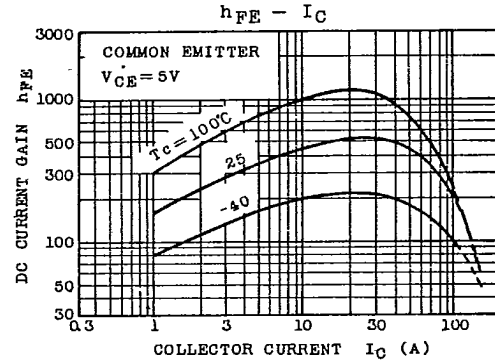
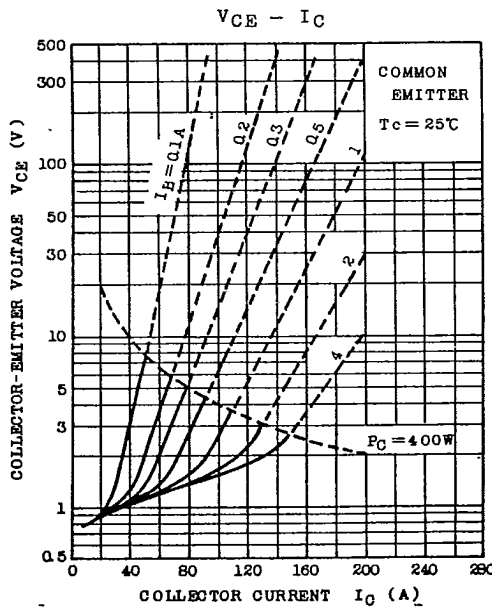
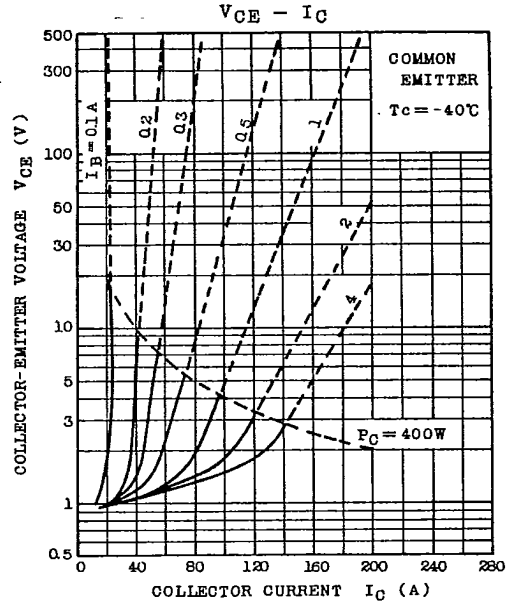
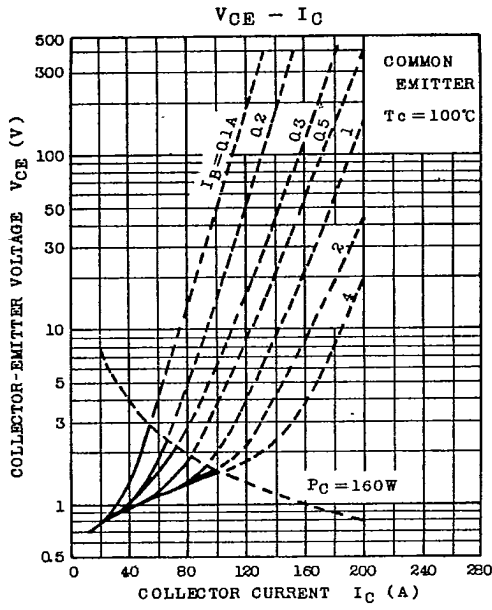
TOSHIBA CORPORATION

GT1A2A



SEMICONDUCTOR
TECHNICAL DATA

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MG100G2CL1
MG100G2DL1



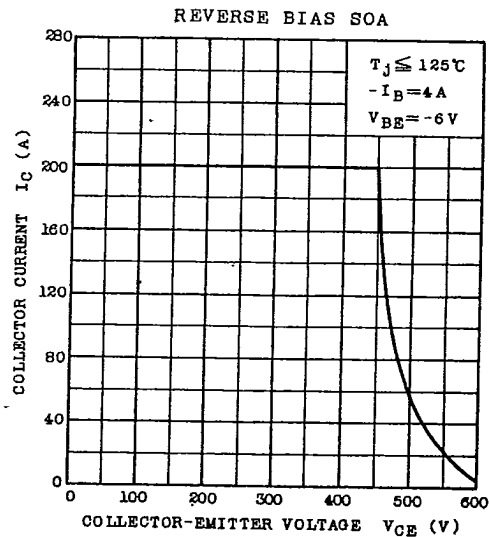
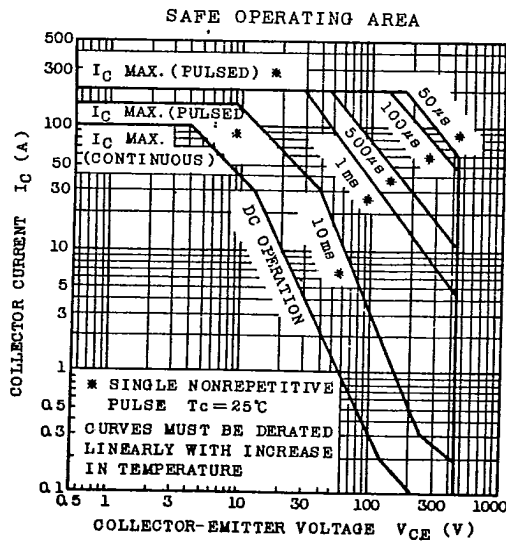
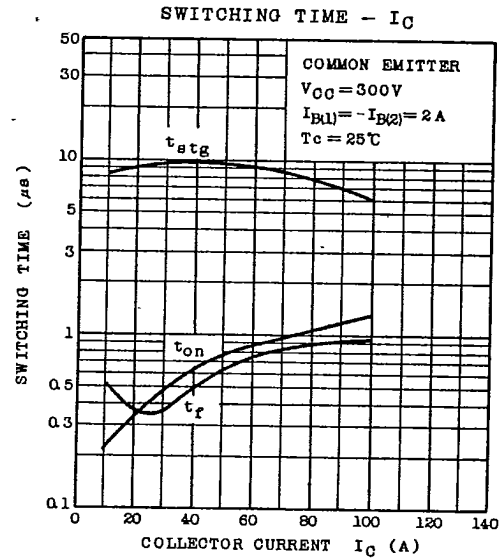
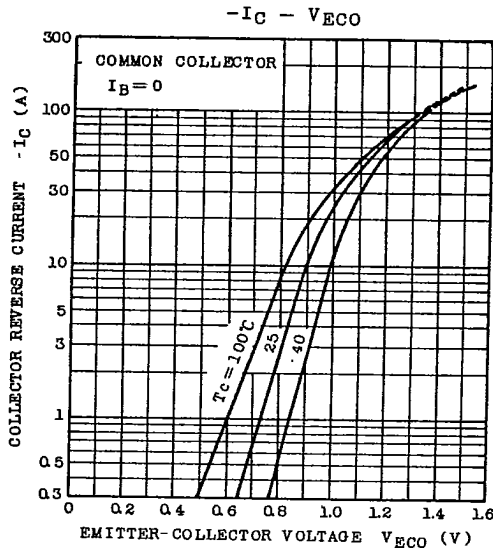
TOSHIBA CORPORATION

GT1A2A



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TECHNICAL DATA

MG100G1JL1
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TOSHIBA CORPORATION

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9097250 TOSHIBA (DISCRETE/OPTO)

90D 16264

DT-33-35

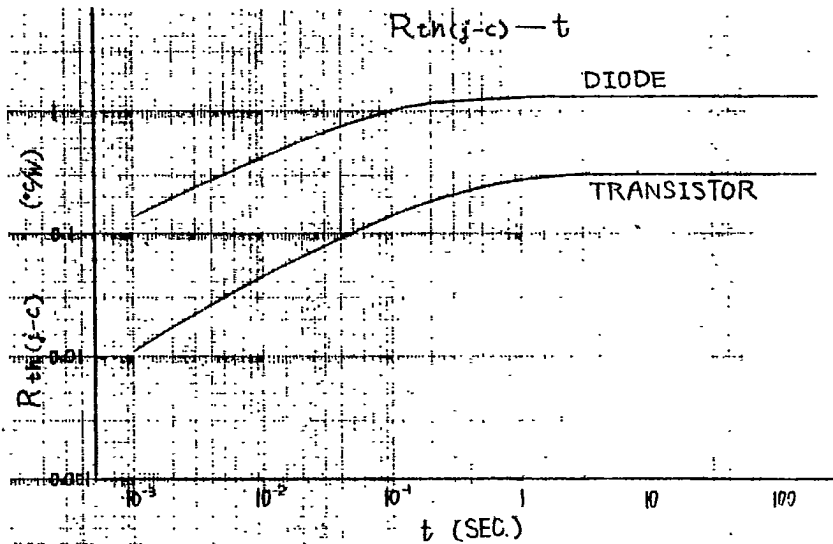
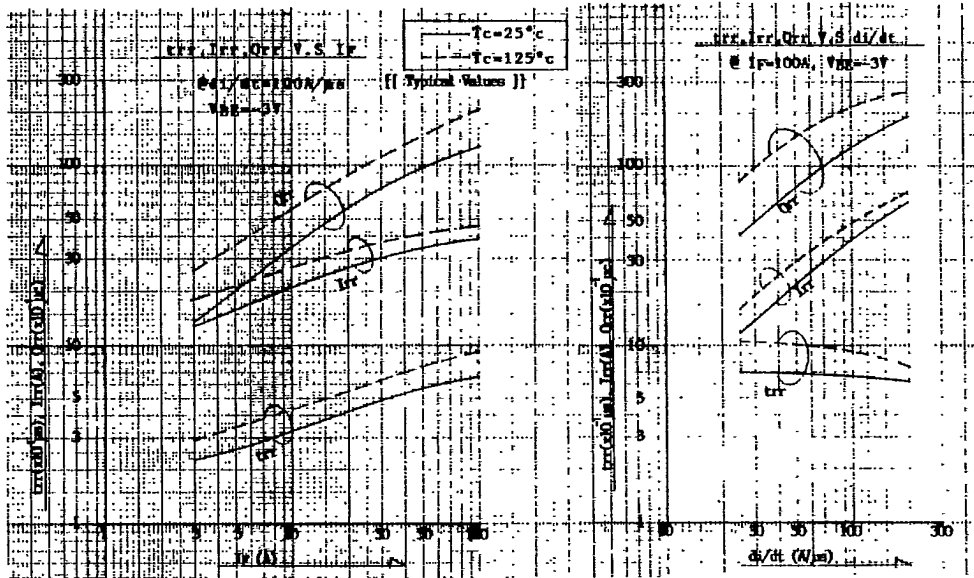


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TECHNICAL DATA

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MG100G2CL1

MG100G2DL1



TOSHIBA CORPORATION

GT1A2A